

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	PATENT APPLICATION
Inventors: Jong-Jan Lee, Sheng Teng Hsu,)	
Douglas J. Tweet and Jer-Shen)	
Maa)	
Serial No.: Not Yet Assigned)	Attorney Docket No.
Filed: Herewith)	SLA 0733
Title: STRAINED SILICON finFET)	
DEVICE)	

Honorable Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

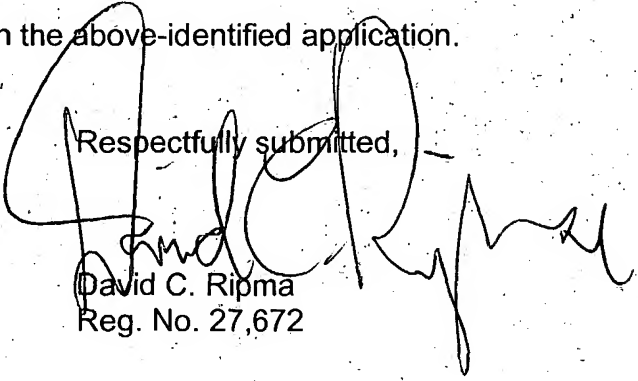
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

(Date) 6/23/03

Respectfully submitted,


David C. Ripma
Reg. No. 27,672

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	
		Filing Date	06-23-03
		First Named Inventor	Sheng Teng Hsu
		Group Art Unit	
		Examiner Name	
Sheet 2 of 3	Attorney Docket Number	SLA0733	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		N. SUGIYAMA, T. MIZUNO, S. TAKAGI, M. KOIKE, A. KUROBE, <i>Formation of strained-silicon layer on thin relaxed SiGe/SiO₂/Si structure using SIMOX technology</i> , Thin Solid Films, 396 (2000) 199-202.	
		M.T. CURRIE, C.W. LEITZ, T.A. LANGDO, G. TARASCHI, E.A. FITZGERALD, D.A. ANTONIADIS, <i>Carrier mobilities and process stability of strained Si n- and p- MOSFETs on SiGe virtual substrate</i> , J. Vac. Sci. Technol. B 19 (6), Nov/Dec 2001, pp 2268-2279.	
		T. TEZUKA, N. SUGIYAMA, T. MIZUNO, S. TAKAGI, <i>High performance strained-Si-on-insulator MOSFETs by novel fabrication processes utilizing Ge-condensation technique</i> , 2002 Symposium on VLSI Technology, Digest of Technical paper.	
		T. MIZUNO, N. SUGIYAMA, T. TEZUKA, T. NUMATA, S. TAKAGI, <i>High performance CMOS operation of strained-SOI MOSFETs using thin film SiGe-on-insulator substrate</i> , 2002 Symposium on VLSI Technology, Digest of Technical paper.	
		K. BRUNNER, H. DOBLER, G. ABSTREITER, H. SCHÄFER, B. LUSTIG, <i>Molecular beam epitaxy growth and thermal stability of Si_{1-x}Ge_x layers on extremely thin silicon-on-insulator substrates</i> , Thin Solid Films, 321 (1998) 245-250.	
		X. HUANG, W-C. LEE, C. KUO, D. HISAMOTO, L. CHANG, J. KEDZIERSKI, E. ANDERSON, H. TAKEUCHI, Y-K. CHOI, K. ASANO, V. SUBRAMANIAN, T-J. KING, J. BOKOR, C. HU, <i>Sub 50-nm finFET: PMOS</i> , IEDM Tech. Dig., p. 67-70, 1999.	
		D. HISAMOTO, W-C. LEE, J. KEDZIERSKI, H. TAKEUCHI, K. ASANO, C. KUO, E. ANDERSON, T-J. KING, J. BOKOR, C. HU, <i>FinFET - A self-aligned double-gate MOSFET scalable to 20 nm</i> , IEEE Transactions on Electron Devices, Vol. 47, No. 12, Dec 2000, pp. 2320-2325	
		Y-K. CHOI, N. LINDERT, P. XUAN, S. TANG, D. HA, E. ANDERSON, T-J. KING, J. BOKOR, C. HU, <i>Sub-20 nm CMOS finFET technologies</i> , IEDM Tech. Dig., 2001.	

Examiner Signature	Date	Considered
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			T ²
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		<p>X. HUANG, W-C. LEE, C. KUO, D. HISAMOTO, L. CHANG, J. KEDZIERSKI, E. ANDERSON, H. TAKEUCHI, Y-K. CHOI, K. ASANO, V. SUBRAMANIAN, T-J. KING, J. BOKOR, C. HU, <i>Sub 50-nm p-channel finFET</i>, IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pp. 880-886.</p> <p>F-L. YANG, H-Y. CHEN, F-C. CHEN, Y-L. CHAN, K-N. YANG, C-J. CHEN, H-J. TAO, Y-K. CHOI, M-S. LIANG, C. HU, <i>35 nm CMOS finFETs</i>, 2002 Symposium on VLSI Technology, Digest of Technical paper.</p>	

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